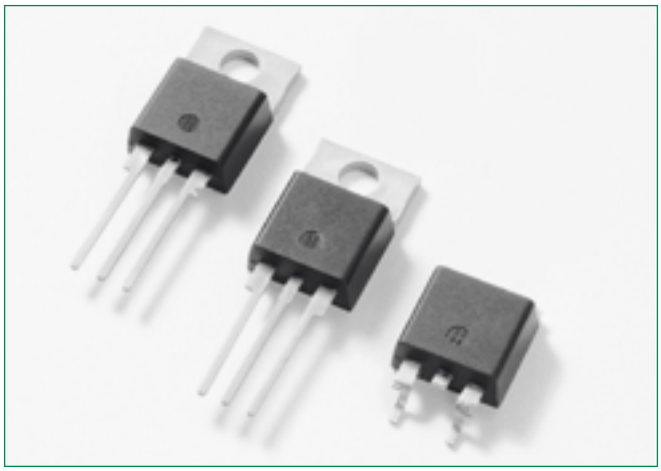
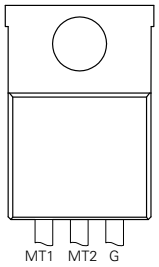
QJxx10xHx and QJxx10xx Series

10 A High Temperature Alternistor and Standard (High Communication) TRIACs

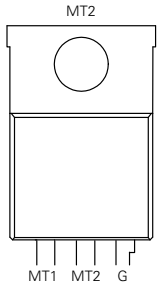


Pinout Diagram

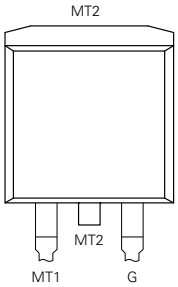
TO-220AB (L-Package)



TO-220AB (R-Package)



TO-263AB



MT1: Main Terminal 1; **MT2**: Main Terminal 2; **G**: Gate

Description

This 10 A high temperature Alternistor and Standard TRIAC series, offered in TO-220AB, TO-220 isolated, and TO-263 packages, has 150°C maximum junction temperature and 120 A I_{TSM} (60 Hz).

This series enables easier thermal management and higher surge handling capability in AC power control applications such as heater control, motor speed control, lighting controls, and static switching relays. Alternistor TRIAC operates in Quadrants I, II, and III, and offers high performance in applications requiring high commutation capability.

Features

- Recognized to UL 1557 as an Electrically Isolated Semiconductor Device
- Glass-passivated junctions
- Surge capability up to 120 A and 60 Hz
- L package UL recognized under E71639 for Electrical isolated at 2500 V_{RMS}
- No contacts to wear out from reaction of switching events
- Solid-state switching eliminates arcing or contact bounce that creates voltage transients
- Restricted (or limited) RFI generation, depending on activation point sine wave
- Requires only a small gate activation pulse in each half-cycle
- RoHS compliant

Applications

- Excellent for AC switching and phase control applications such as heating, lighting, and motor speed controls. Typical applications are AC solid-state switches, light dimmers, power tools, lawn care equipment, home/brown goods, and white goods appliances.
- Alternistor TRIACs (no snubber required) are used in applications with extremely inductive loads requiring highest commutation performance.
- Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.
- Standard type devices normally operate in Quadrants I & III triggered from AC line.

Product Summary

Characteristic	Value	Unit
$I_{T(RMS)}$	10	A
V_{DRM}/V_{RRM}	600 or 800	V
$I_{GT\ (Q1)}$	10 to 50	mA

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10 A High Temperature Alternistor and Standard (High Communication) TRIACs

Maximum Ratings — Alternistor TRIAC (3 Quadrants)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	QJxx10LHy	T_C = 120°C	10	A
		QJxx10RHy QJxx10NHy	T_C = 130°C		
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_{VJ} initial = 25°C)	f = 50 Hz, t = 20 ms		100	A
		f = 60 Hz, t = 16.7 ms		120	
I^2t	I^2t Value for fusing	t_p = 8.3 ms		60	A^2s
di/dt	Critical rate of rise of on-state current	f = 60 Hz, T_{VJ} = 150°C		70	A/µs
I_{GTM}	Peak gate trigger current	t_p = 20 µs, T_{VJ}= 150°C		4	A
$P_{G(AV)}$	Average gate power dissipation	T_{VJ} = 150°C		0.5	W
T_{stg}	Storage temperature range	-		-40 to 150	°C
T_{VJ}	Operating junction temperature range	-		-40 to 150	°C
V_{DSM}/V_{RSM}	Peak Non-repetitive Blocking Voltage	Pulse Width = 100 µs	600 V	V_{DRM}/V_{RRM} + 100	V
			800 V	V_{DRM}/V_{RRM} + 200	

Maximum Ratings — Standard TRIAC

Symbol	Parameter			Value	Unit
$V_{DSM}//V_{RSM}$	Peak non-repetitive blocking voltage	Pulse Width =100 µs	600 V	V_{DRM}/V_{RRM} + 100 V	V
			800 V	V_{DRM}/V_{RRM} + 200 V	
$I_{T(RMS)}$	RMS on-state current (full sine wave)	QJxx10Ly	T_C = 120°C	10	A
		QJxx10Ry/QJxx10Ny	T_C = 130°C		
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_{VJ} initial = 25°C)	f = 50 Hz, t = 20 ms	QJxx10xy	100	A
		f = 60 Hz, t = 16.7 ms	QJxx10xy	120	
I^2t	I^2t Value for fusing	t_p = 8.3 ms	QJxx10xy	60	A^2s
di/dt	Critical rate of rise of on-state current I_G = 200 mA with ≤ 0.1 µs rise time	f = 60 Hz, T_{VJ} =150 °C		70	A/µs
I_{GTM}	Peak gate trigger current	t_p = 20 µs, T_{VJ} =150 °C		4	A/µs
$P_{G(AV)}$	Average gate power dissipation	T_{VJ} =150 °C		0.5	W
T_{stg}	Storage temperature range	-		-40 to 150	°C
T_{VJ}	Operating junction temperature range	-		-40 to 150	°C

Note: xx=voltage/10, x=package, y=sensitivity

Thermal Characteristics

Symbol	Parameter		Value	Unit
R_{thJC}	Thermal Resistance, junction-to-case (AC)	QJxx10RHy/QJxx10NHy QJxx10Ry/QJxx10Ny	1.2	K/W
		QJxx10LHy/QJxx10Ly	2.3	
R_{thJA}	Thermal Resistance, junction-to-ambient (AC)	QJxx10RHy/QJxx10Ry	45	K/W
		QJxx10LHy/QJxx10Ly	90	

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QJxx10xHx and QJxx10xx Series

10 A High Temperature Alternistor and Standard (High Communication) TRIACs

Electrical Characteristics (T_{VJ} = 25°C, unless otherwise specified) — Alternistor TRIAC (3 Quadrants)

Symbol	Description	Conditions		QJxx10xH3			QJxx10xH4			QJxx10xH5			Unit
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
I_{GT}	DC Gate Trigger Current	V_D = 12 V, R_L = 60 Ω	I-II-III	-	-	10	-	-	35	-	-	50	mA
V_{GT}	DC Gate Trigger Voltage	V_D = 12 V, R_L = 60 Ω	I-II-III	-	-	1.3	-	-	1.3	-	-	1.3	V
V_{GD}	Gate Non-trigger Voltage	$V_D = V_{DRM}$, R_L = 3.3 kΩ, T_{VJ} = 150 °C	I-II-III	0.2	-	-	0.2	-	-	0.2	-	-	V
I_H	Holding Current	I_T = 100 mA		-	-	15	-	-	40	-	-	50	mA
dv/dt	Critical Rate-of-rise of Off-stage Voltage	$V_D = V_{DRM}$, Gate Open, T_{VJ} = 150 °C	600 V	100	-	-	250	-	-	350	-	-	V/µs
			800 V	150	-	-	450	-	-	700	-	-	
		V_D = 2/3 V_{DRM}, Gate Open, T_{VJ} = 150 °C	600 V	150	-	-	300	-	-	500	-	-	
			800 V	200	-	-	600	-	-	1000	-	-	
(dv/dt)c		(di/dt)/c = 6.5 A/ms, T_{VJ} = 150 °C		10	-	-	20	-	-	30	-	-	V/µs
t_{gt}	Turn-on Time	I_G = 2 x I_{GT}, P_W = 15 µs, I_T = 14.1 A(pk)		-	4	-	-	-	7	-	-	9	-

Electrical Characteristics (T_{VJ} = 25°C, unless otherwise specified) — Standard TRIAC

Symbol	Description	Conditions	Quadrant		Value		Unit
					Qxx10x4	Qxx10x5	
I_{GT}	DC Gate Trigger Current	V_D = 12 V R_L = 60 Ω	I – II – III	MAX.	25	50	mA
			IV	TYP.	50	75	
V_{GT}	DC Gate Trigger Voltage	V_D = 12 V R_L = 60 Ω	ALL	MAX.	1.3		V
V_{GD}	Gate Non-trigger Voltage	$V_D = V_{DRM}$ R_L = 3.3 kΩ T_{VJ} = 150°C	ALL	MIN.	0.2		V
I_H	Holding Current	I_T = 100 mA		MAX.	35	50	mA
dv/dt	Critical Rate-of-rise of Off-stage Voltage	$V_D = V_{DRM}$ Gate Open T_{VJ} = 150°C	600 V	MIN.	400	800	V/µs
			800 V		600	1000	
		V_D = 2/3 V_{DRM} Gate Open T_{VJ} = 150°C	600 V		600	1000	
			800 V		800	1200	
(dv/dt)c		(di/dt)c = 6.5 A/ms T_{VJ} = 150°C		TYP.	3	4	V/µs
t_{gt}	Turn-on Time	I_G = 2 x I_{GT} P_W = 15 µs I_T = 14.1 A(pk)	I – II – III	TYP.	1-2-6	1-2-6	µs
			IV		10	11	

Static Characteristics

Symbol	Description	Conditions	Maximum Value	Unit
V_{TM}	Peak On-state Voltage	I_{TM} = 14.1A t_p = 380 µs	1.60	V
I_{DRM}/I_{RRM}	Off-state Current, Peak Repetitive	$V_D = V_{DRM} = V_{RRM}$, T_{VJ} = 25°C	10	µA
		$V_D = V_{DRM} = V_{RRM}$, T_{VJ} = 150°C	4	mA

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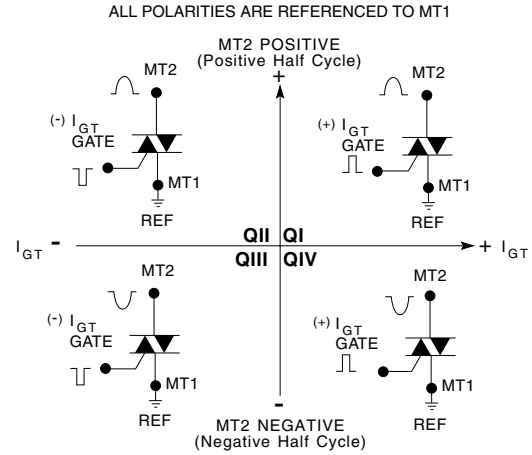
Figure 1: Definition of Quadrants



Note: Alternistors will not operate in QIV

Figure 2. Normalized DC Gate Trigger Current for all Quadrants vs. Junction Temperature

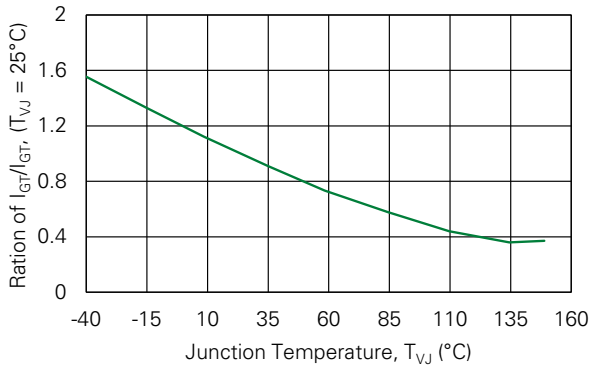


Figure 3. Normalized DC Holding Current vs. Junction Temperature

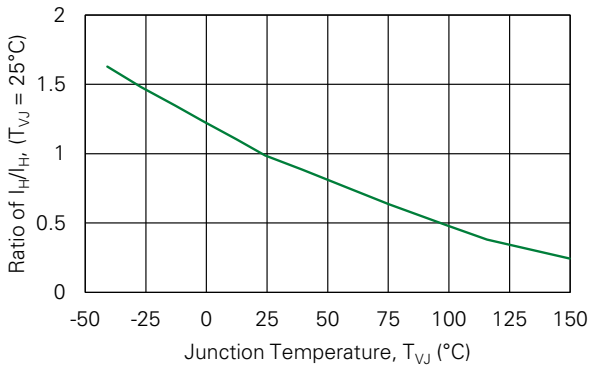


Figure 4. Normalized DC Gate Trigger Voltage for all Quadrants vs. Junction Temperature

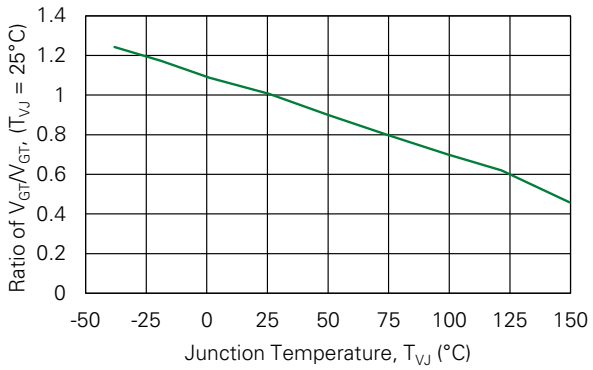


Figure 5. Typical Power Dissipation vs. RMS On-state Current

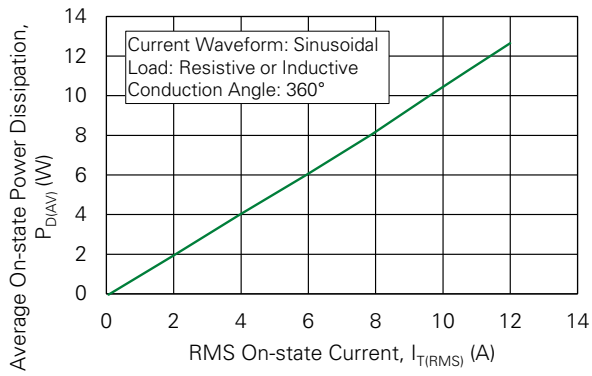


Figure 6. Maximum Allowable Case Temperature vs. On-state Current

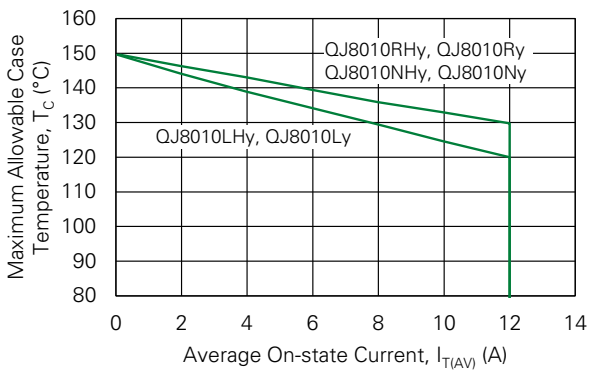


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Figure 7. Typical On-state Current vs. On-state Voltage

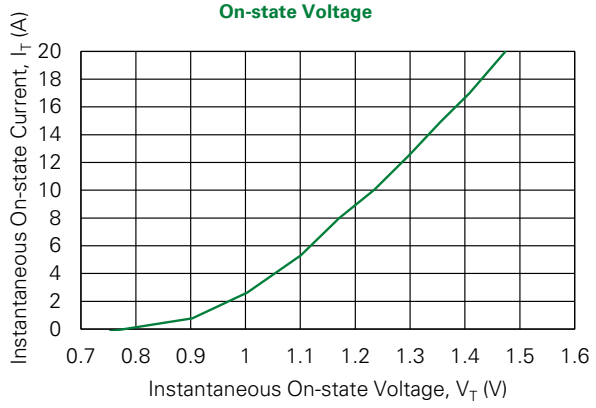
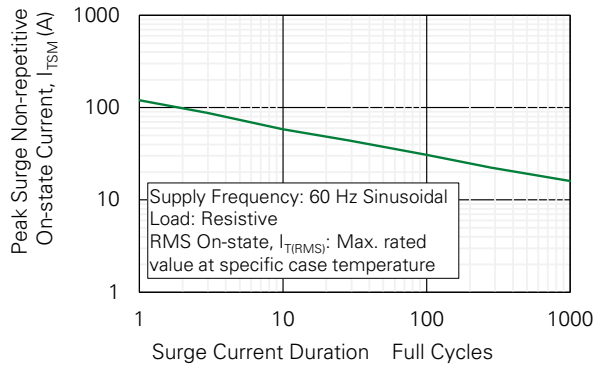


Figure 8. Surge Peak On-state Current vs.Number of Cycles



Notes:
1. Gate control may be lost during and immediately following surge current interval.
2. Overload may not be repeated until junction temperature has returned to steady-state rated value

QJxx10xHx and QJxx10xx Series

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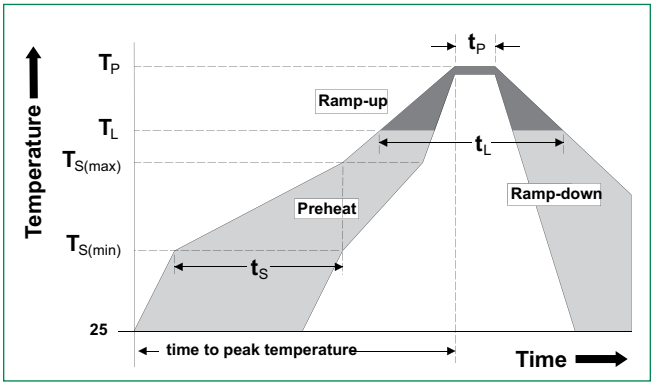
Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	**- Temperature Min ($T_{s(min)}$)**	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 to 180 s
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{S(max)}$ to T_L - Ramp-up Rate		5°C/second max
Reflow	**- Temperature (T_L) (Liquidus)**	217°C
	- Time (min to max) (t_s)	60 to 150 seconds
Peak Temperature (T_P)		260 °C (±5 °C)
Time within 5°C of actual peak Temperature (t_p)		20 to 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_P)		8 minutes Max.
Do not exceed		280°C



Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL Recognized epoxy meeting flammabilty classification 94V-0.
Terminal Material	Copper Alloy

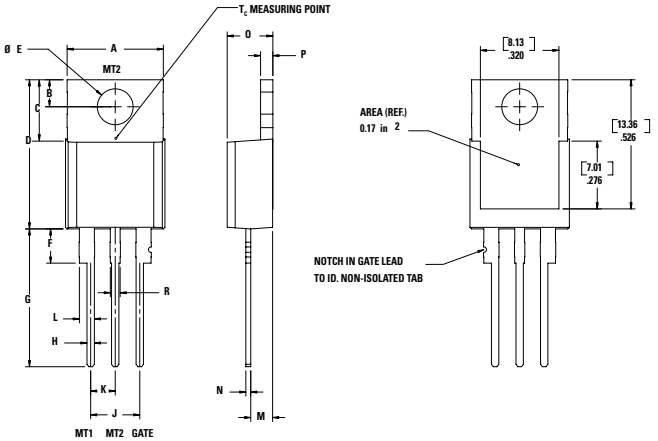
Design Considerations

Careful selection of the correct component for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the component rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C, 15-min dwell-time
Temperature/Humidity	EIA/JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3 Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

Dimensions - TO-220AB (R-Package) - Non-Isolated Mounting Tab Common with Center Lead



Note: Maximum torque to be applied to mounting tab is 8 in-lbs. (0.904 Nm).

Dimension	Milimeters		Inches	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

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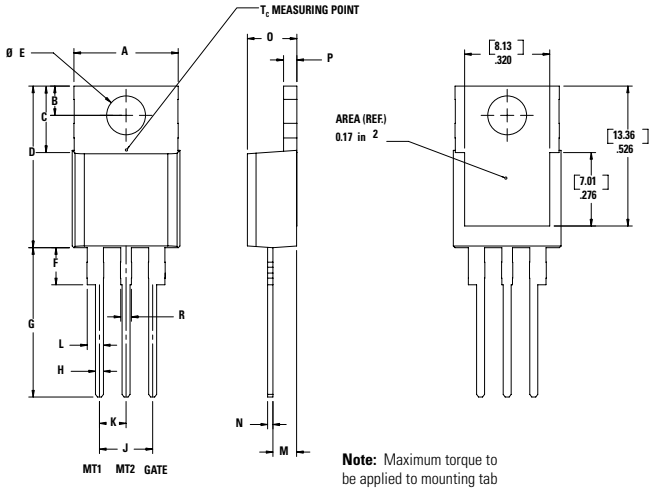
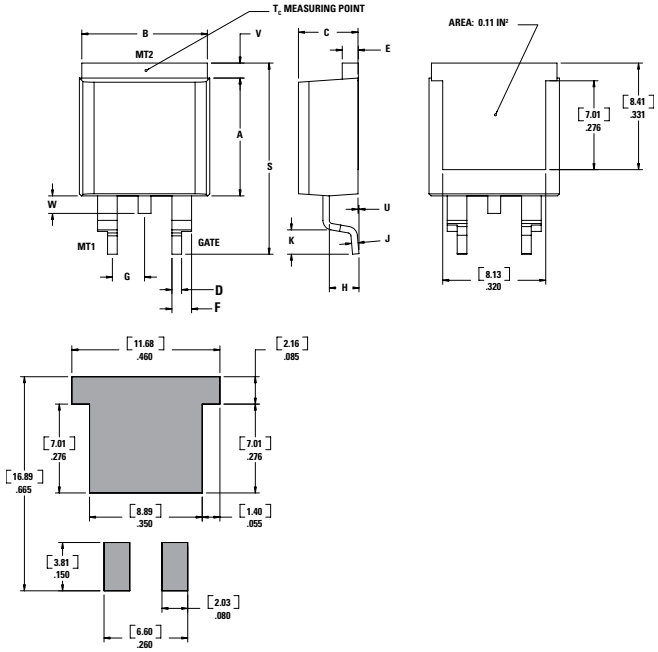
Dimensions - TO-220AB (L-Package) - Isolated Mounting Tab



Note: Maximum torque to be applied to mounting tab is 8 in-lbs. (0.904 Nm).

Dimension	Milimeteres		Inches	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

Dimensions - TO-263AB (N-Package) - D2-PAK Surface Mount



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
E	0.045	0.060	1.14	1.52
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.092	0.102	2.34	2.59
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.88
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

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Part Numbering System

QJ 80 10 L H4 56

Component Type
QJ: High T_{VJ} TRIAC or Alternistor

Voltage Rating
60: 600 V
80: 800 V

Current Rating
10: 10 A

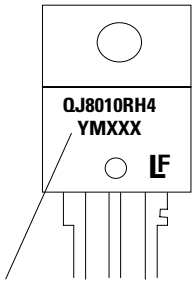
Package Type
L: TO-220 Isolated
R: TO-220 Non-Isolated
N: TO-263 (D^2Pak)

Sensitivity & Type
H3: 10 mA (QI, II, III)
H4: 35 mA (QI, II, III)
H5: 50 mA (QI, II, III)
4: 25 mA (QI, II, III)
50 mA (QIV)
5: 50 mA (QI, II, III)

Lead Form Dimensions
xx: Lead Form Option

Part Marking System

TO-220 AB - (L and R Package)
TO-263 AB - (N Package)



Date Code Marking
Y: Year Code
M: Month Code
XXX: Lot Trace Code

Product Selector

Part Number	Voltage		Gate Sensitivity Quadrants		Type	Package
	600 V	800 V	I – II – III	IV		
QJxx10LH3	x	x	10 mA	-	Alternistor TRIAC	TO-220L
QJxx10RH3	x	x	10 mA	-	Alternistor TRIAC	TO-220R
QJxx10NH3	x	x	10 mA	-	Alternistor TRIAC	TO-263 D^2PAK
QJxx10LH4	x	x	35 mA	-	Alternistor TRIAC	TO-220L
QJxx10RH4	x	x	35 mA	-	Alternistor TRIAC	TO-220R
QJxx10NH4	x	x	35 mA	-	Alternistor TRIAC	TO-263 D^2PAK
QJxx10LH5	x	x	50 mA	-	Alternistor TRIAC	TO-220L
QJxx10RH5	x	x	50 mA	-	Alternistor TRIAC	TO-220R
QJxx10NH5	x	x	50 mA	-	Alternistor TRIAC	TO-263 D^2PAK
QJxx10L4	x	x	25 mA	50 mA	Standard TRIAC	TO-220L
QJxx10R4	x	x	25 mA	50 mA	Standard TRIAC	TO-220R
QJxx10N4	x	x	25 mA	50 mA	Standard TRIAC	TO-263 D^2PAK
QJxx10L5	x	x	50 mA	TYP 75 mA	Standard TRIAC	TO-220L
QJxx10R5	x	x	50 mA	TYP 75 mA	Standard TRIAC	TO-220R
QJxx10N5	x	x	50 mA	TYP 75 mA	Standard TRIAC	TO-263 D^2PAK

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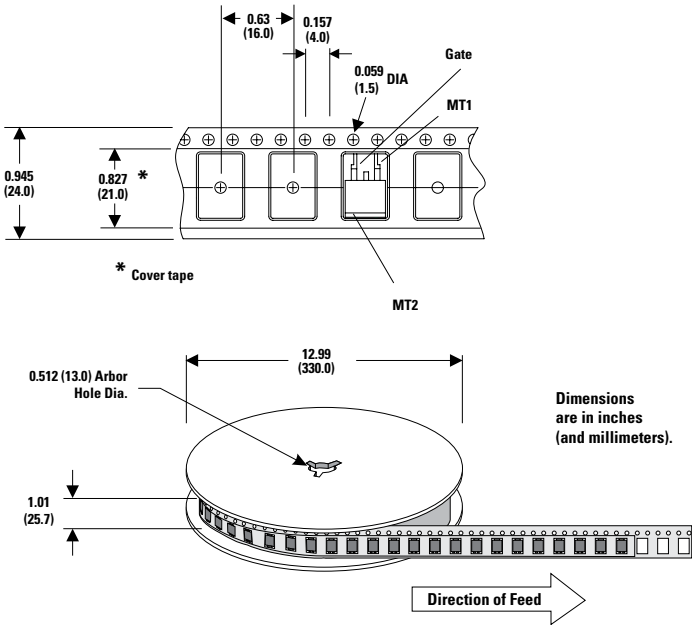
Packing Options

Part Number	Marking	Weight	Packing Mode	M.O.Q
QJxx10RHyTP	QJxx10RHy	2.2 g	Tube Pack	1000 (50 per tube)
QJxx10LHyTP	QJxx10LHy	2.2 g	Tube Pack	1000 (50 per tube)
QJxx10NHyTP	QJxx10NHy	1.6 g	Tube Pack	1000 (50 per tube)
QJxx10NHyRP	QJxx10NHy	1.6 g	Embossed Carrier	500
QJxx10LyTP	QJxx10Ly	2.2 g	Tube Pack	1000 (50 per tube)
QJxx10RyTP	QJxx10Ry	2.2 g	Tube Pack	1000 (50 per tube)
QJxx10NyTP	QJxx10Ny	1.6 g	Tube Pack	1000 (50 per tube)
QJxx10NyRP	QJxx10Ny	1.6 g	Embossed Carrier	500

TO-263 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards



IXYS

Part of: Littelfuse
Expertise Applied | Answers Delivered

Revised: TK. 01/18/24